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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, Ethernet, I²C, IrDA, LINbus, Memory Card, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	140
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	132K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f207iet6

The backup registers are 32-bit registers used to store 80 bytes of user application data when V_{DD} power is not present. Backup registers are not reset by a system, a power reset, or when the device wakes up from the Standby mode (see *Section 3.18: Low-power modes*).

Like backup SRAM, the RTC and backup registers are supplied through a switch that is powered either from the V_{DD} supply when present or the V_{BAT} pin.

3.18 Low-power modes

The STM32F20x family supports three low-power modes to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

- **Sleep mode**

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Stop mode**

  The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the 1.2 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.

  The device can be woken up from the Stop mode by any of the EXTI line. The EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm / wakeup / tamper / time stamp events, the USB OTG FS/HS wakeup or the Ethernet wakeup.

- **Standby mode**

  The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.2 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, the SRAM and register contents are lost except for registers in the backup domain and the backup SRAM when selected.

  The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm / wakeup / tamper /time stamp event occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped when the device enters the Stop or Standby mode.

3.19 V_{BAT} operation

The V_{BAT} pin allows to power the device V_{BAT} domain from an external battery or an external supercapacitor.

V_{BAT} operation is activated when V_{DD} is not present.

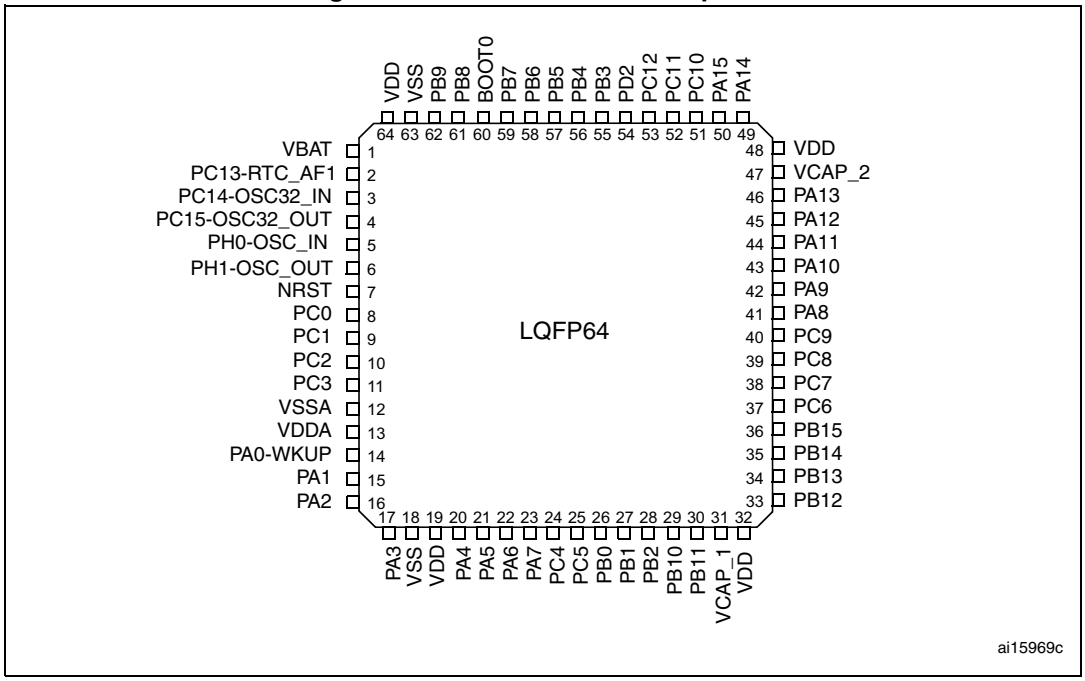
The V_{BAT} pin supplies the RTC, the backup registers and the backup SRAM.

Note: When the microcontroller is supplied from V_{BAT}, external interrupts and RTC alarm/events do not exit it from V_{BAT} operation.

When using WLCSP64+2 package, if IRROFF pin is connected to V_{DD}, the V_{BAT} functionality is no more available and V_{BAT} pin should be connected to V_{DD}.

4 Pinouts and pin description

Figure 10. STM32F20x LQFP64 pinout



1. The above figure shows the package top view.

Figure 11. STM32F20x WLCSP64+2 ballout

	1	2	3	4	5	6	7	8	9
A	PA14	PA15	PC12	PB3	PB5	PB7	PB9	VDD	V_{BAT}
B	VSS	PA13	PC10	PB4	PB6	BOOT0	PB8	PC13	PC14
C	PA12	VCAP_2	PC11				PD2	IRROFF	PC15
D	PC9	PA11	PA10				PC2	VSS	VDD
E	VDD	PA8	PA9				PA0	NRST	PH0-OSC_IN
F	VSS	PC7	PC8				VREF+	PC1	PH1-OSC_OUT
G	PB15	PC6	PC5				PA3	PC3	PC0
H	PB14	PB13	PB10	PC4	PA6	PA5	REGOFF	PA1	VSS_5
J	PB12	PB11	VCAP_1	PB2	PB1	PB0	PA7	PA4	PA2

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1. The above figure shows the package top view.

Table 10. Alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF014	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/I2C2/I2C3	SPI1/SPI2/I2S2	SPI3/I2S3	USART1/2/3	UART4/5/ USART6	CAN1/CAN2/ TIM12/13/14	OTG_FS/ OTG_HS	ETH	FSMC/SDIO/ OTG_HS	DCMI		
Port F	PF0	-	-	-	-	I2C2_SDA	-	-	-	-	-	-	-	FSMC_A0	-	-	EVENTOUT
	PF1	-	-	-	-	I2C2_SCL		-	-	-	-	-	-	FSMC_A1	-	-	EVENTOUT
	PF2	-	-	-	-	I2C2_SMBA	-	-	-	-	-	-	-	FSMC_A2	-	-	EVENTOUT
	PF3	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A3	-	-	EVENTOUT
	PF4	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A4	-	-	EVENTOUT
	PF5	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A5	-	-	EVENTOUT
	PF6	-	-	-	TIM10_CH1	-	-	-	-	-	-	-	-	FSMC_NIORD	-	-	EVENTOUT
	PF7	-	-	-	TIM11_CH1	-	-	-	-	-	-	-	-	FSMC_NREG	-	-	EVENTOUT
	PF8	-	-	-	-	-	-	-	-	-	TIM13_CH1	-	-	FSMC_NIOWR	-	-	EVENTOUT
	PF9	-	-	-	-	-	-	-	-	-	TIM14_CH1	-	-	FSMC_CD	-	-	EVENTOUT
	PF10	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_INTR	-	-	EVENTOUT
	PF11	-	-	-	-	-	-	-	-	-	-	-	-		DCMI_D12	-	EVENTOUT
	PF12	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A6	-	-	EVENTOUT
	PF13	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A7	-	-	EVENTOUT
	PF14	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A8	-	-	EVENTOUT
	PF15	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A9	-	-	EVENTOUT
Port G	PG0	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A10	-	-	EVENTOUT
	PG1	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A11	-	-	EVENTOUT
	PG2	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A12	-	-	EVENTOUT
	PG3	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A13	-	-	EVENTOUT
	PG4	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A14	-	-	EVENTOUT
	PG5	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A15	-	-	EVENTOUT
	PG6	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_INT2	-	-	EVENTOUT
	PG7	-	-	-	-	-	-	-	-	USART6_CK	-	-	-	FSMC_INT3	-	-	EVENTOUT
	PG8	-	-	-	-	-	-	-	-	USART6_RTS	-	-	ETH _PPS_OUT	-	-	-	EVENTOUT
	PG9	-	-	-	-	-	-	-	-	USART6_RX	-	-	-	FSMC_NE2/ FSMC_NCE3	-	-	EVENTOUT
	PG10	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_NCE4_1/ FSMC_NE3	-	-	EVENTOUT
	PG11	-	-	-	-	-	-	-	-	-	-	-	ETH _MII_TX_EN ETH _RMII_TX_EN	FSMC_NCE4_2	-	-	EVENTOUT
	PG12	-	-	-	-	-	-	-	-	USART6_RTS	-	-	-	FSMC_NE4	-	-	EVENTOUT
	PG13	-	-	-	-	-	-	-	-	UART6_CTS	-	-	ETH _MII_TXD0 ETH _RMII_TXD0	FSMC_A24	-	-	EVENTOUT
	PG14	-	-	-	-	-	-	-	-	USART6_TX	-	-	ETH _MII_TXD1 ETH _RMII_TXD1	FSMC_A25	-	-	EVENTOUT
	PG15	-	-	-	-	-	-	-	-	USART6_CTS	-	-	-	-	DCMI_D13	-	EVENTOUT

Table 15. Limitations depending on the operating power supply range

Operating power supply range	ADC operation	Maximum Flash memory access frequency ($f_{Flashmax}$)	Number of wait states at maximum CPU frequency (f_{CPUmax}= 120 MHz)(1)	I/O operation	FSMC_CLK frequency for synchronous accesses	Possible Flash memory operations
V_{DD} =1.8 to 2.1 V(2)	Conversion time up to 1 Msps	16 MHz with no Flash memory wait state	7(3)	– Degraded speed performance – No I/O compensation	Up to 30 MHz	8-bit erase and program operations only
V_{DD} = 2.1 to 2.4 V	Conversion time up to 1 Msps	18 MHz with no Flash memory wait state	6(3)	– Degraded speed performance – No I/O compensation	Up to 30 MHz	16-bit erase and program operations
V_{DD} = 2.4 to 2.7 V	Conversion time up to 2 Msps	24 MHz with no Flash memory wait state	4(3)	– Degraded speed performance – I/O compensation works	Up to 48 MHz	16-bit erase and program operations
V_{DD} = 2.7 to 3.6 V(4)	Conversion time up to 2 Msps	30 MHz with no Flash memory wait state	3(3)	– Full-speed operation – I/O compensation works	– Up to 60 MHz when V_{DD} = 3.0 to 3.6 V – Up to 48 MHz when V_{DD} = 2.7 to 3.0 V	32-bit erase and program operations

1. The number of wait states can be reduced by reducing the CPU frequency (see *Figure 21*).
2. On devices in WLCSP64+2 package, if IRROFF is set to V_{DD}, the supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range using an external power supply supervisor (see *Section 3.16*).
3. Thanks to the ART accelerator and the 128-bit Flash memory, the number of wait states given here does not impact the execution speed from Flash memory since the ART accelerator allows to achieve a performance equivalent to 0 wait state program execution.
4. The voltage range for OTG USB FS can drop down to 2.7 V. However it is degraded between 2.7 and 3 V.

6.3.3 Operating conditions at power-up / power-down (regulator ON)

Subject to general operating conditions for T_A.

Table 17. Operating conditions at power-up / power-down (regulator ON)

Symbol	Parameter	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	20	∞	µs/V
	V_{DD} fall time rate	20	∞	

6.3.4 Operating conditions at power-up / power-down (regulator OFF)

Subject to general operating conditions for T_A.

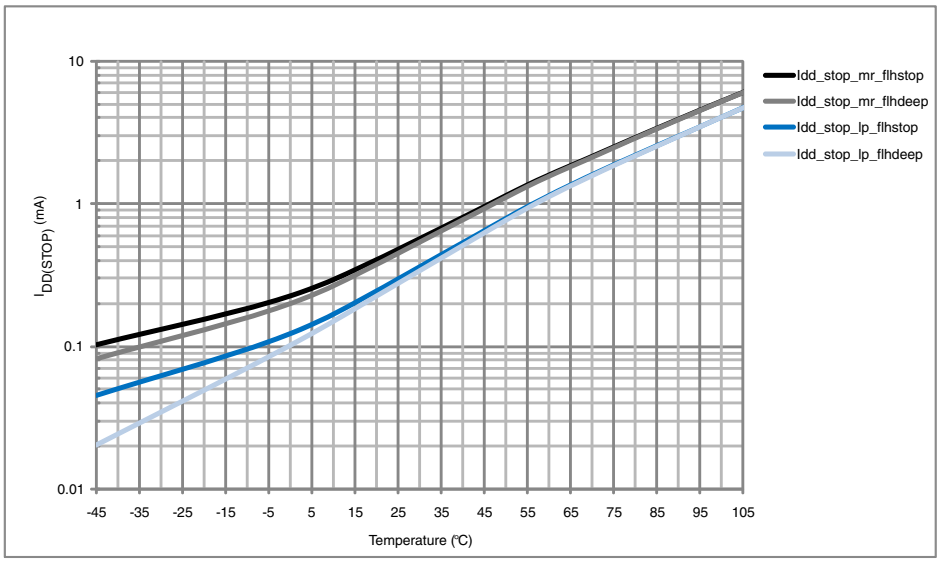
Table 18. Operating conditions at power-up / power-down (regulator OFF)

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	Power-up	20	∞	µs/V
	V_{DD} fall time rate	Power-down	20	∞	
t_{VCAP}	V_{CAP_1} and V_{CAP_2} rise time rate	Power-up	20	∞	
	V_{CAP_1} and V_{CAP_2} fall time rate	Power-down	20	∞	

Table 23. Typical and maximum current consumptions in Stop mode

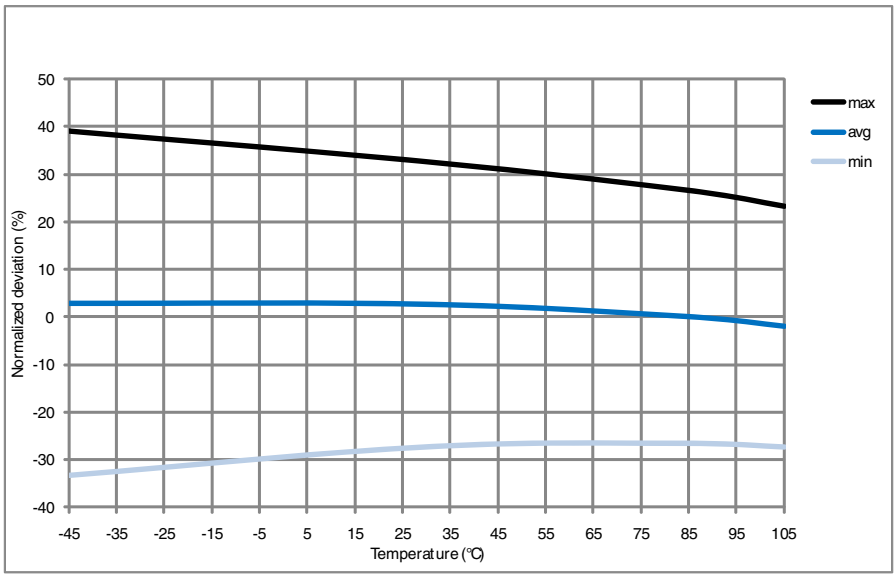
Symbol	Parameter	Conditions	Typ	Max			Unit
			T_A = 25 °C	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD_STOP}	Supply current in Stop mode with main regulator in Run mode	Flash in Stop mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.55	1.2	11.00	20.00	mA
		Flash in Deep power down mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.50	1.2	11.00	20.00	
	Supply current in Stop mode with main regulator in Low-power mode	Flash in Stop mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.35	1.1	8.00	15.00	
		Flash in Deep power down mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.30	1.1	8.00	15.00	

Figure 29. Typical current consumption vs. temperature in Stop mode



1. All typical and maximum values from table 18 and figure 26 will be reduced over time by up to 50% as part of ST continuous improvement of test procedures. New versions of the datasheet will be released to reflect these changes

Figure 35. ACC_{LSI} versus temperature



6.3.10 PLL characteristics

The parameters given in *Table 34* and *Table 35* are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Table 34. Main PLL characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PLL_IN}	PLL input clock(1)	-	0.95(2)	1	2.10(2)	MHz
f_{PLL_OUT}	PLL multiplier output clock	-	24	-	120	MHz
f_{PLL48_OUT}	48 MHz PLL multiplier output clock	-	-	-	48	MHz
f_{VCO_OUT}	PLL VCO output	-	192	-	432	MHz
t_{LOCK}	PLL lock time	VCO freq = 192 MHz	75	-	200	µs
		VCO freq = 432 MHz	100	-	300	

6.3.11 PLL spread spectrum clock generation (SSCG) characteristics

The spread spectrum clock generation (SSCG) feature allows to reduce electromagnetic interferences (see *Table 42: EMI characteristics*). It is available only on the main PLL.

Table 36. SSCG parameters constraint

Symbol	Parameter	Min	Typ	Max(1)	Unit
f_{Mod}	Modulation frequency	-	-	10	KHz
md	Peak modulation depth	0.25	-	2	%
MODEPER * INCSTEP	-	-	-	$2^{15}-1$	-

1. Guaranteed by design, not tested in production.

Equation 1

The frequency modulation period (MODEPER) is given by the equation below:

$$MODEPER = round[f_{PLL\_IN} / (4 \times f_{Mod})]$$

f_{PLL_IN} and f_{Mod} must be expressed in Hz.

As an example:

If f_{PLL_IN} = 1 MHz and f_{MOD} = 1 kHz, the modulation depth (MODEPER) is given by equation 1:

$$MODEPER = round[10^6 / (4 \times 10^3)] = 250$$

Equation 2

Equation 2 allows to calculate the increment step (INCSTEP):

$$INCSTEP = round[((2^{15} - 1) \times md \times PLLN) / (100 \times 5 \times MODEPER)]$$

f_{VCO_OUT} must be expressed in MHz.

With a modulation depth (md) = ±2 % (4 % peak to peak), and PLLN = 240 (in MHz):

$$INCSTEP = round[((2^{15} - 1) \times 2 \times 240) / (100 \times 5 \times 250)] = 126md(quantitazed)\%$$

An amplitude quantization error may be generated because the linear modulation profile is obtained by taking the quantized values (rounded to the nearest integer) of MODPER and INCSTEP. As a result, the achieved modulation depth is quantized. The percentage quantized modulation depth is given by the following formula:

$$md_{quantized}\% = (MODEPER \times INCSTEP \times 100 \times 5) / ((2^{15} - 1) \times PLLN)$$

As a result:

$$md_{quantized}\% = (250 \times 126 \times 100 \times 5) / ((2^{15} - 1) \times 240) = 2.0002\%(peak)$$

Figure 36 and *Figure 37* show the main PLL output clock waveforms in center spread and down spread modes, where:

F0 is f_{PLL_OUT} nominal.

T_{mode} is the modulation period.

md is the modulation depth.

Figure 36. PLL output clock waveforms in center spread mode

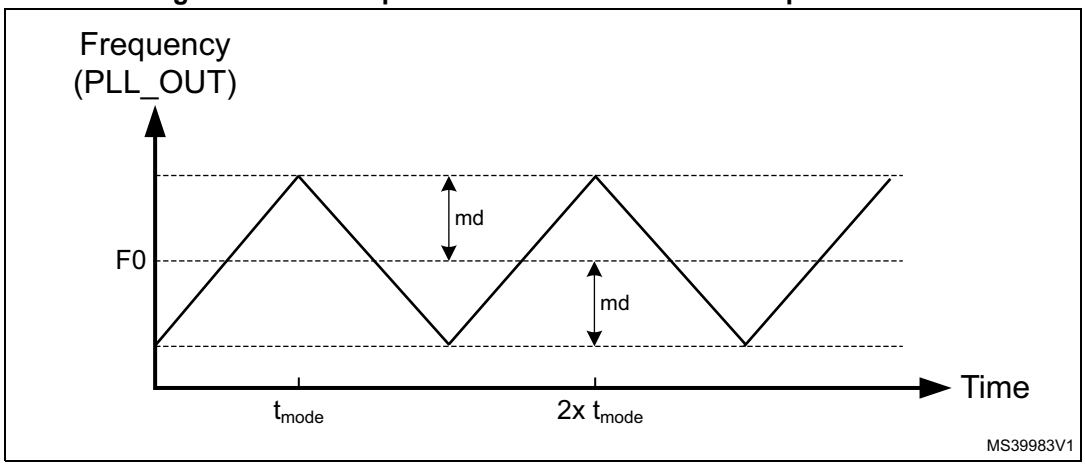
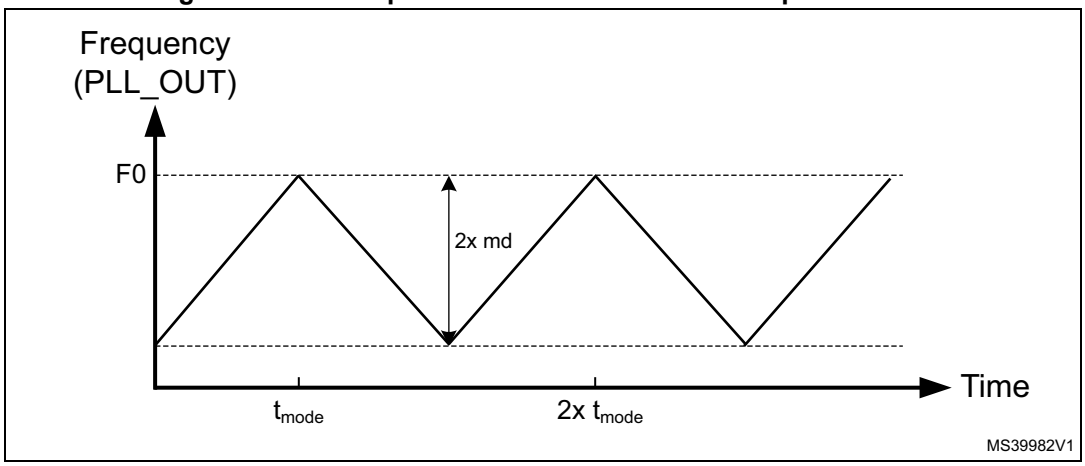


Figure 37. PLL output clock waveforms in down spread mode



6.3.12 Memory characteristics

Flash memory

The characteristics are given at T_A = –40 to 105 °C unless otherwise specified.

6.3.16 I/O port characteristics

General input/output characteristics

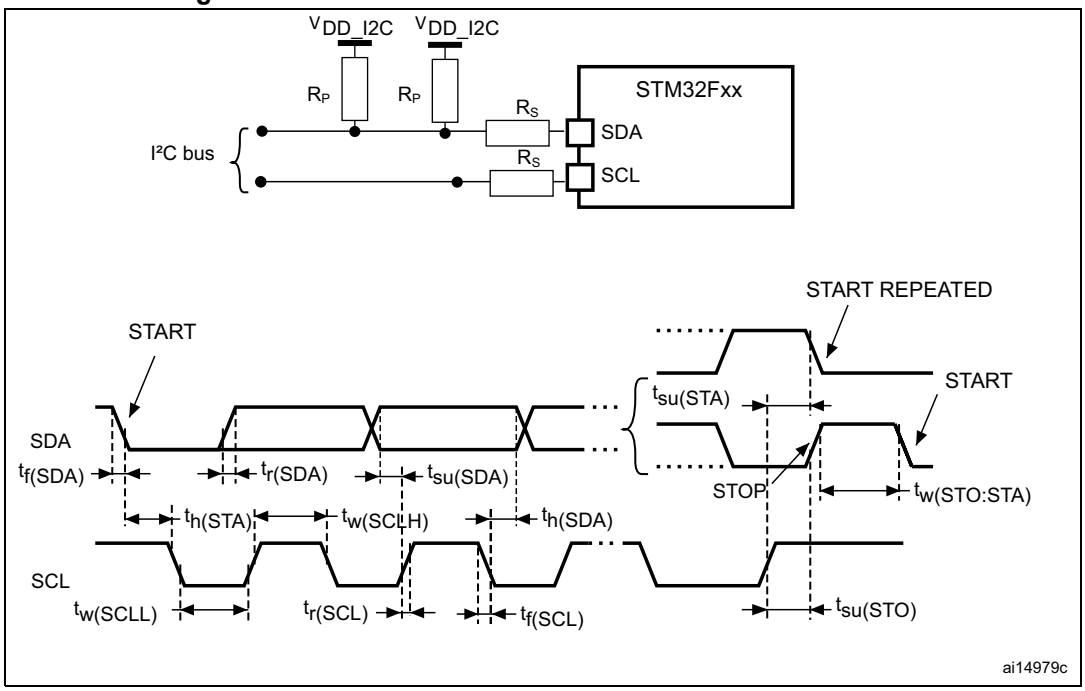
Unless otherwise specified, the parameters given in *Table 50* are derived from tests performed under the conditions summarized in *Table 14: General operating conditions*.

All I/Os are CMOS and TTL compliant.

Table 46. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	FT, TTa and NRST I/O input low level voltage	1.7 V≤V_{DD}≤3.6 V	-	-	$0.35V_{DD}-0.04^{(1)}$ $0.3V_{DD}^{(2)}$	V
	BOOT0 I/O input low level voltage	1.75 V≤V_{DD} ≤3.6 V, –40 °C≤T_A ≤105 °C	-	-	$0.1V_{DD}+0.1^{(1)}$	
		1.7 V≤V_{DD} ≤3.6 V, 0 °C≤T_A ≤105 °C	-	-		
V_{IH}	FT, TTa and NRST I/O input high level voltage(5)	1.7 V≤V_{DD}≤3.6 V	$0.45V_{DD}+0.3^{(1)}$ $0.7V_{DD}^{(2)}$	-	-	V
	BOOT0 I/O input high level voltage	1.75 V≤V_{DD} ≤3.6 V, –40 °C≤T_A ≤105 °C	$0.17V_{DD}+0.7^{(1)}$	-	-	
		1.7 V≤V_{DD} ≤3.6 V, 0 °C≤T_A ≤105 °C				
V_{HYS}	FT, TTa and NRST I/O input hysteresis	1.7 V≤V_{DD}≤3.6 V	$0.45V_{DD}+0.3^{(1)}$	-	-	V
	BOOT0 I/O input hysteresis	1.75 V≤V_{DD} ≤3.6 V, –40 °C≤T_A ≤105 °C	$10\%V_{DDIO}^{(1)(3)}$	-	-	
		1.7 V≤V_{DD} ≤3.6 V, 0 °C≤T_A ≤105 °C	$100^{(1)}$	-	-	
I_{lkg}	I/O input leakage current (4)	V_{SS} ≤V_{IN} ≤V_{DD}	-	-	±1	µA
	I/O FT input leakage current (5)	V_{IN} = 5 V	-	-	3	

Figure 41. I²C bus AC waveforms and measurement circuit



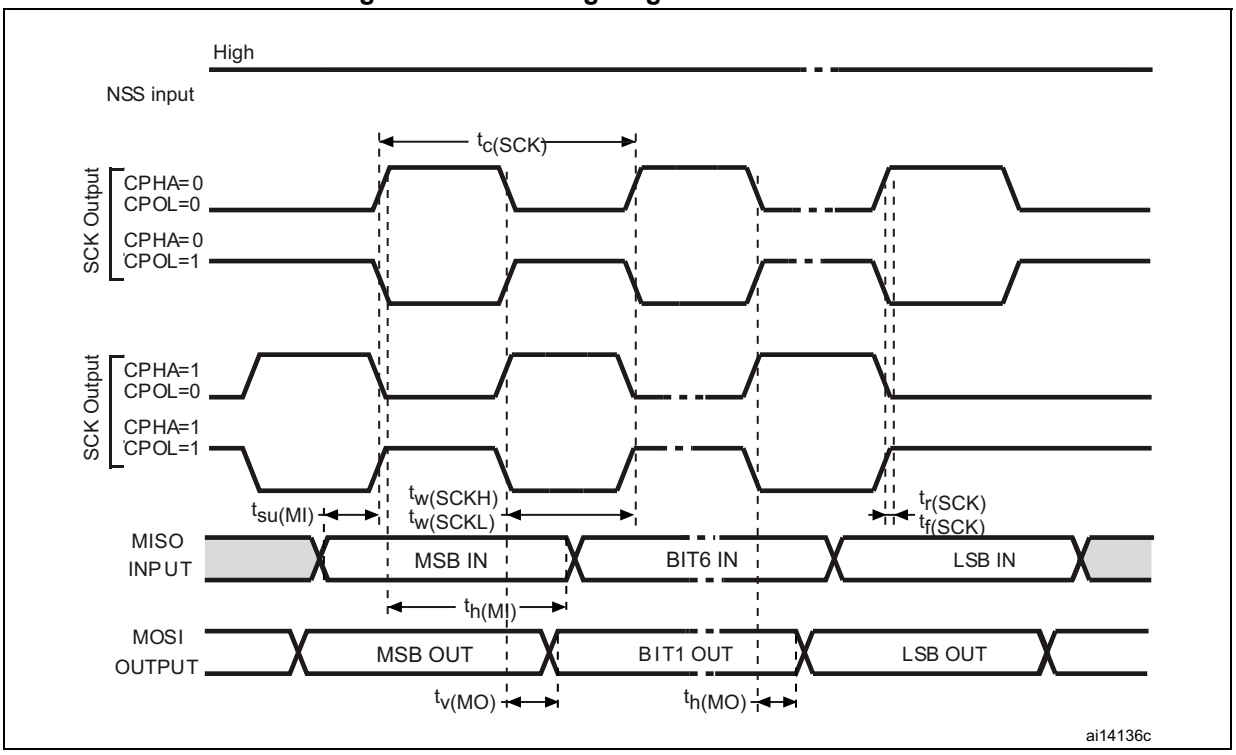
1. R_S= series protection resistor.
2. R_P = external pull-up resistor.
3. V_{DD_I2C} is the I²C bus power supply.

Table 53. SCL frequency (f_{PCLK1}= 30 MHz.,V_{DD} = 3.3 V)(1)(2)

f_{SCL} (kHz)	I2C_CCR value
	R_P = 4.7 kΩ
400	0x8019
300	0x8021
200	0x8032
100	0x0096
50	0x012C
20	0x02EE

1. R_P = External pull-up resistance, f_{SCL} = I²C speed,
2. For speeds around 200 kHz, the tolerance on the achieved speed is of ±5%. For other speed ranges, the tolerance on the achieved speed ±2%. These variations depend on the accuracy of the external components used to design the application.

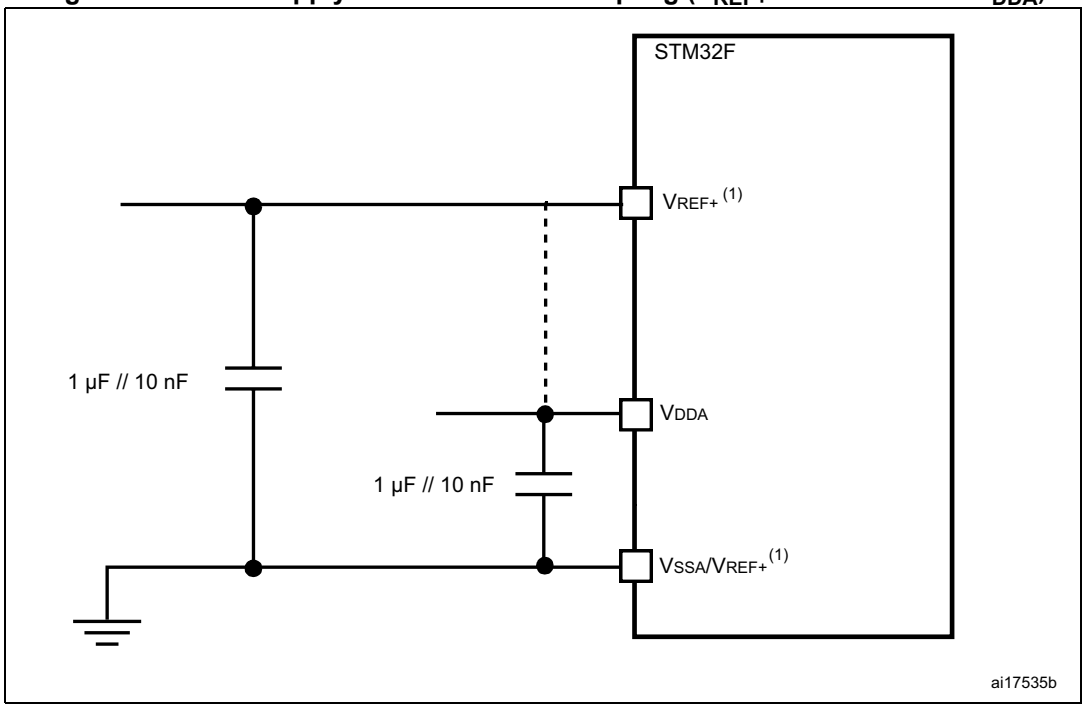
Figure 44. SPI timing diagram - master mode



General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 54* or *Figure 55*, depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.

Figure 54. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are both available on UFBGA176 package. V_{REF+} is also available on all packages except for LQFP64. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA}.

Table 77. Synchronous multiplexed PSRAM write timings(1)(2) (continued)

Symbol	Parameter	Min	Max	Unit
$t_{d(CLKL-NWEL)}$	FSMC_CLK low to FSMC_NWE low	-	1	ns
$t_{d(CLKL-NWEH)}$	FSMC_CLK low to FSMC_NWE high	0	-	ns
$t_{d(CLKL-ADIV)}$	FSMC_CLK low to FSMC_AD[15:0] invalid	0	-	ns
$t_{d(CLKL-DATA)}$	FSMC_A/D[15:0] valid data after FSMC_CLK low	-	2	ns
$t_{d(CLKL-NBLH)}$	FSMC_CLK low to FSMC_NBL high	0.5	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results, not tested in production.

Figure 63. Synchronous non-multiplexed NOR/PSRAM read timings

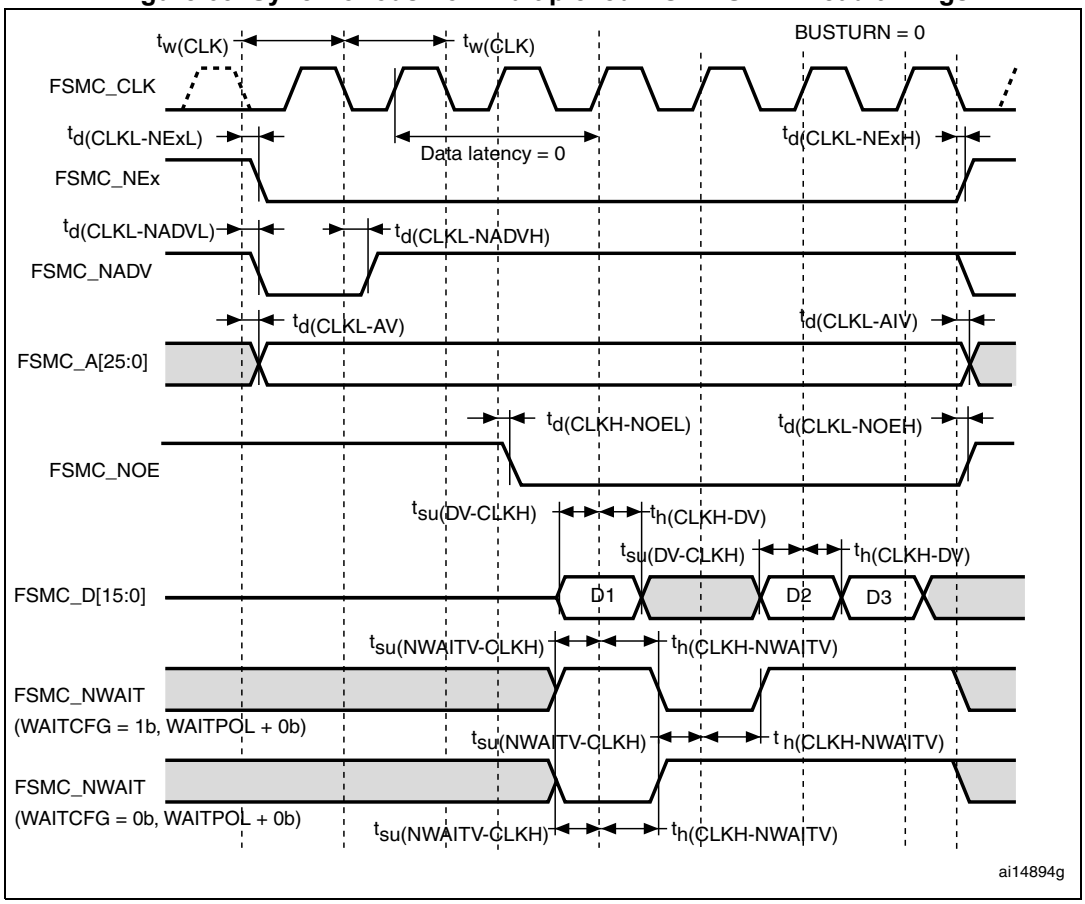
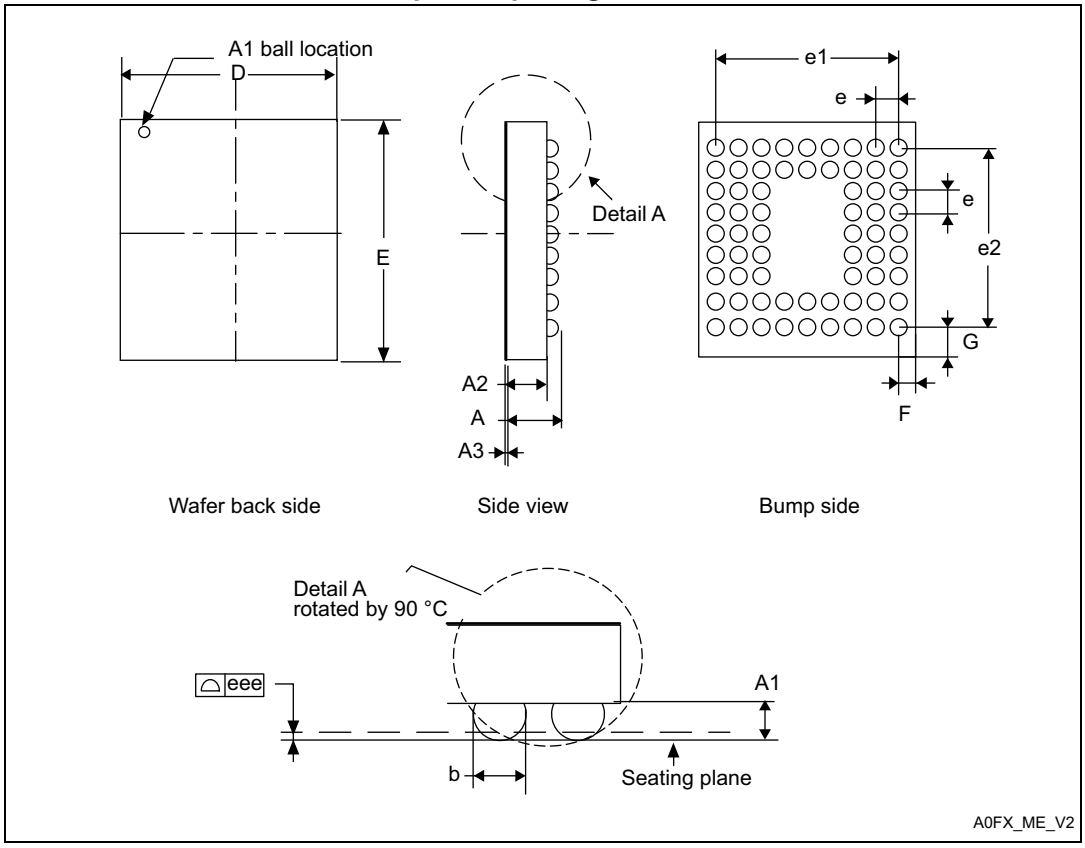


Table 78. Synchronous non-multiplexed NOR/PSRAM read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FSMC_CLK period	$2T_{HCLK}$	-	ns
$t_{d(CLKL-NExL)}$	FSMC_CLK low to FSMC_NEx low (x=0..2)	-	0	ns
$t_{d(CLKL-NExH)}$	FSMC_CLK low to FSMC_NEx high (x= 0…2)	1	-	ns
$t_{d(CLKL-NADVL)}$	FSMC_CLK low to FSMC_NADV low	-	2.5	ns

7.2 WLCSP64+2 package information

Figure 79. WLCSP64+2 - 66-ball, 3.639 x 3.971 mm, 0.4 mm pitch wafer level chip scale package outline



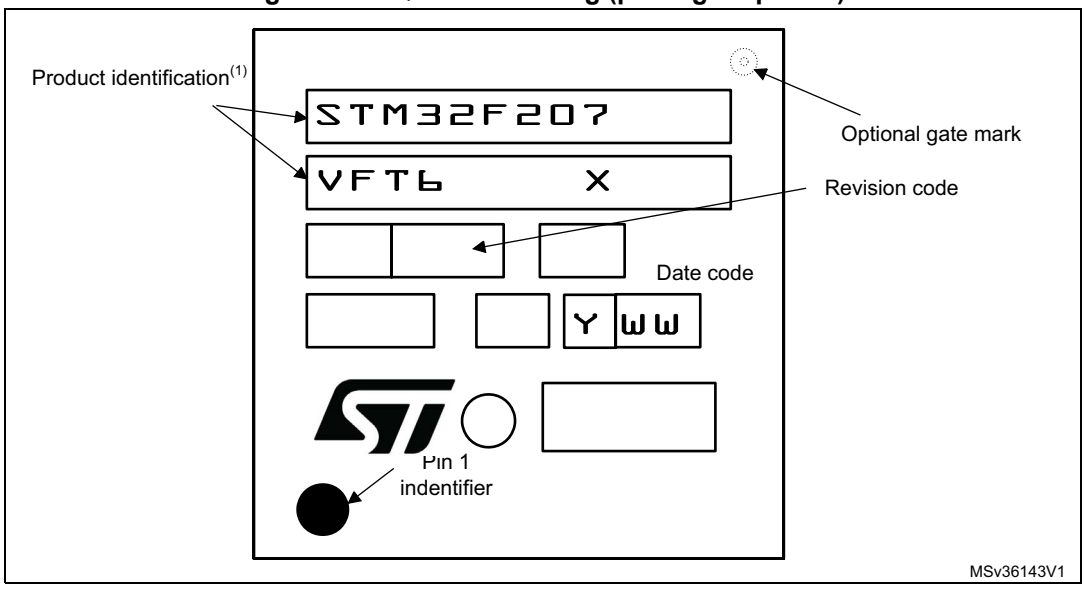
1. Drawing is not to scale.

Table 88. WLCSP64+2 - 66-ball, 4.539 x 4.911 mm, 0.4 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A	0.540	0.570	0.600	0.0213	0.0224	0.0236
A1	-	0.190	-	-	0.0075	-
A2	-	0.380	-	-	0.0150	-
A3	-	0.025	-	-	0.010	-
b(2)	0.240	0.270	0.300	0.0094	0.0106	0.0118
D	3.604	3.939	3.674	0.1419	0.1551	0.1446
E	3.936	3.971	4.006	0.1550	0.1563	0.1577
e	-	0.400	-	-	0.0157	-
e1	-	3.200	-	-	0.1260	-
e2	-	3.200	-	-	0.1260	-

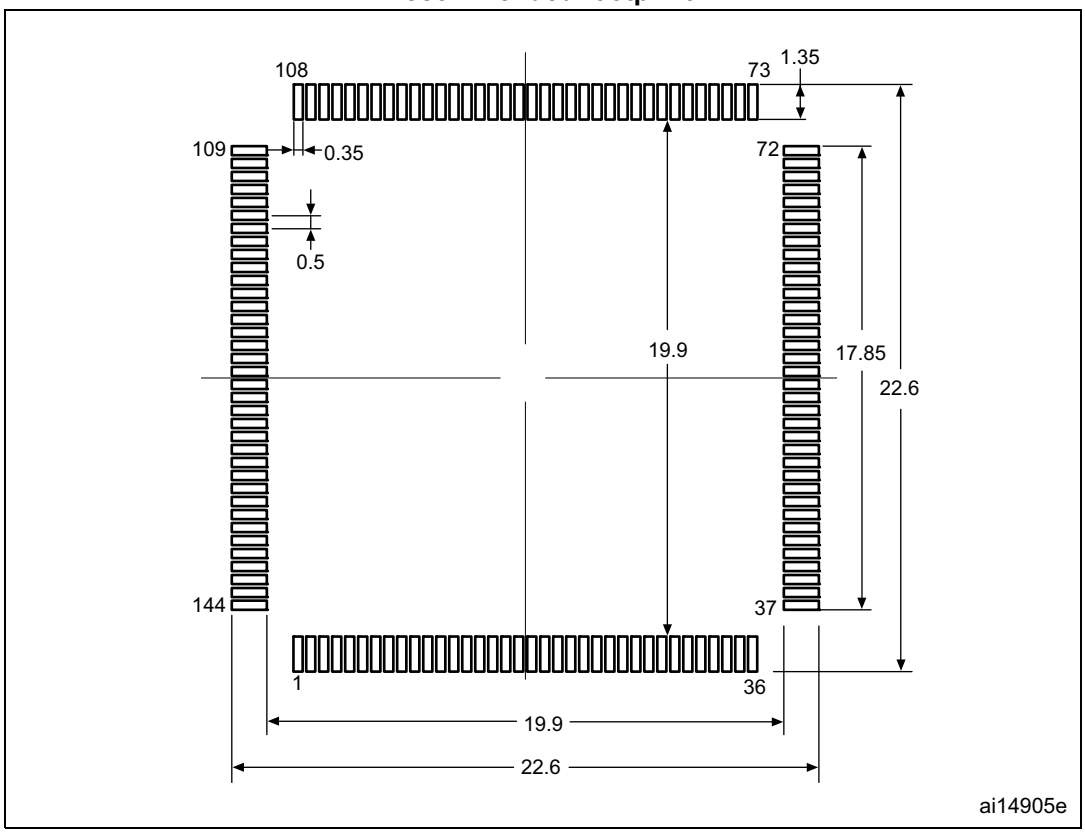
Device marking

Figure 83. LQFP100 marking (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Figure 85. LQFP144 - 144-pin,20 x 20 mm low-profile quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

Table 93. UFBGA176+25, - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 90. UFBGA176+25 - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package recommended footprint

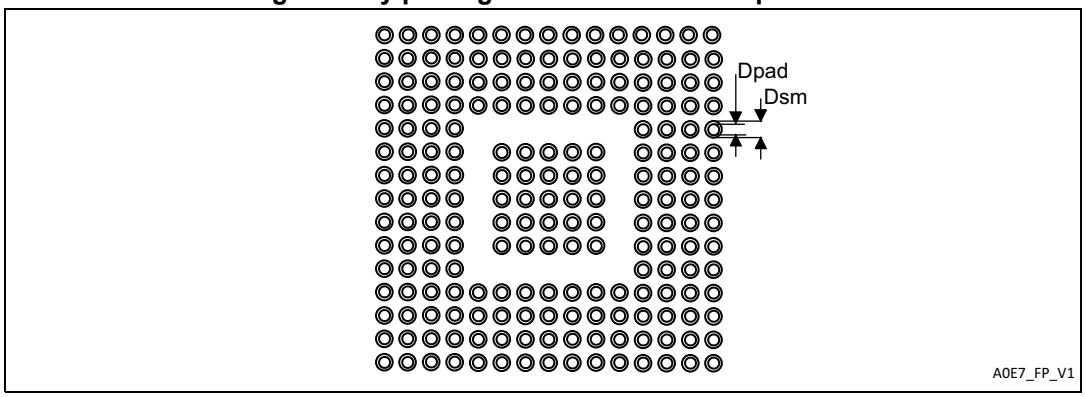


Table 94. UFBGA176+25 recommended PCB design rules (0.65 mm pitch BGA)

Dimension	Recommended values
Pitch	0.65 mm
Dpad	0.300 mm
Dsm	0.400 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.300 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.100 mm